

Description

The SX30P02BF uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

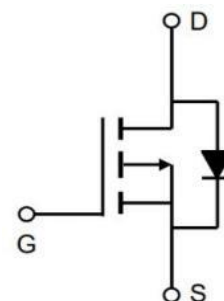
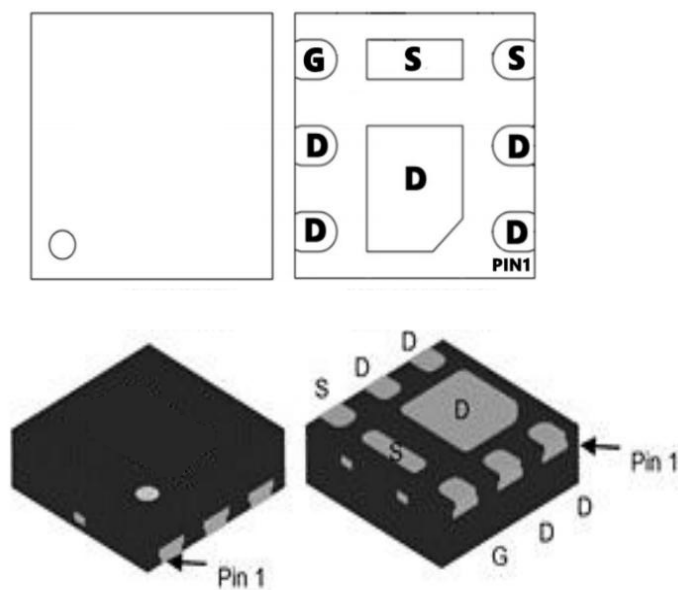
$V_{DS} = -20V$ $I_D = -30A$

$R_{DS(ON)} < 12m\Omega$ @ $V_{GS} = -4.5V$

Application

electronic cigarette

Load switch



Absolute Maximum Ratings ($T_c = 25^\circ C$ unless otherwise noted)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	± 12	V
$I_D @ T_c = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-30	A
$I_D @ T_c = 70^\circ C$	Continuous Drain Current, $V_{GS} @ -4.5V^1$	-21.4	A
IDM	Pulsed Drain Current ²	-90	A
$P_D @ T_c = 25^\circ C$	Total Power Dissipation ³	2.4	W
$P_D @ T_c = 70^\circ C$	Total Power Dissipation ³	19	W
TSTG	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	125	$^\circ C/W$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	6.9	$^\circ C/W$

Electrical Characteristics (T_J=25°C, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
V(BR)DSS	Drain-to-Source breakdown voltage	V _{GS} = 0V, I _D = 250μA	-20	-24	—	V
R _{DS(on)}	Static Drain-to-Source on-resistance	V _{GS} = -4.5V, I _D = -10A	—	9.5	12	mΩ
		V _{GS} = -2.5V, I _D = -8.9A	—	12	16	
		V _{GS} = -1.8V, I _D = -4.5A	—	17	21	
		V _{GS} = -1.8V, I _D = -4.5A	—	17	21	
V _{GS(th)}	Gate threshold voltage	V _{DS} = V _{GS} , I _D = 250μA	-0.4	0.6	-1	V
I _{DSS}	Drain-to-Source leakage current	V _{DS} = -12V, V _{GS} = 0V	—	—	-1	μA
I _{GSS}	Gate-to-Source forward leakage	V _{GS} = 8V	—	—	100	nA
		V _{GS} = -8V	—	—	-100	
g _{FS}	Forward Transconductance	V _{DS} = -5V, I _D = -10A	-3	—	—	S
Q _g	Total gate charge	I _D = -10A, V _{DD} = -6V, V _{GS} = -4.5V	—	21	—	nC
Q _{gs}	Gate-to-Source charge		—	2.5	—	
Q _{gd}	Gate-to-Drain("Miller") charge		—	6	—	
t _{d(on)}	Turn-on delay time	V _{GS} = -4.5V, V _{DD} = -6V, I _D = -10A, R _{GEN} = 6Ω	—	30	—	ns
t _r	Rise time		—	48	—	
t _{d(off)}	Turn-Off delay time		—	97	—	
t _f	Fall time		—	65	—	
C _{iss}	Input capacitance	V _{GS} = 0V V _{DS} = -6V f = 1MHz	—	2138	—	pF
C _{oss}	Output capacitance		—	273	—	
C _{rss}	Reverse transfer capacitance		—	236	—	
I _S	Continuous Source Current (Body Diode)	MOSFET symbol showing the integral reverse p-n junction diode.	—	—	-30	A
I _{SM}	Pulsed Source Current (Body Diode)		—	—	-90	A
V _{SD}	Diode Forward Voltage	I _S = -2A, V _{GS} = 0V	—	-0.77	-1.2	V
t _{rr}	Reverse Recovery Time	T _J = 25°C, I _F = -10A, di/dt = 100A/μs	—	16	—	ns
Q _{rr}	Reverse Recovery Charge	T _J = 25°C, I _F = -10A, di/dt = 100A/μs	—	5.9	—	uC

Notes:

- 1、The maximum current rating is limited by bond-wires.
- 2、Repetitive rating; pulse width limited by max. junction temperature.
- 3、The power dissipation PD is based on max. junction temperature, using junction-to-ambient thermal resistance.
- 4、The value of R_{θJA} is measured with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with TA = 25 °C
- 5、These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T_{J(MAX)} = 150 °C.

Typical Characteristics

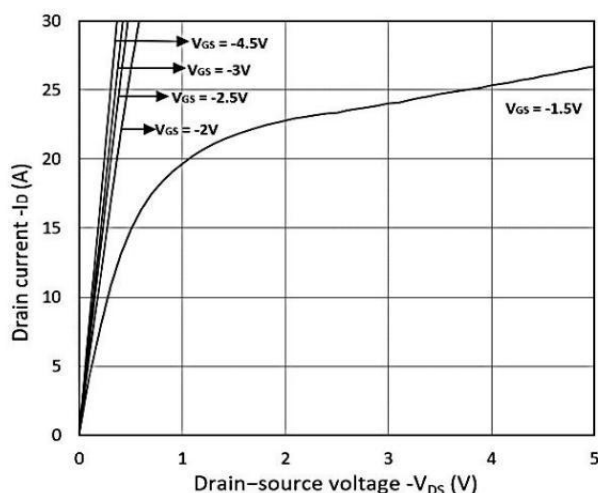


Figure 1. Output Characteristics

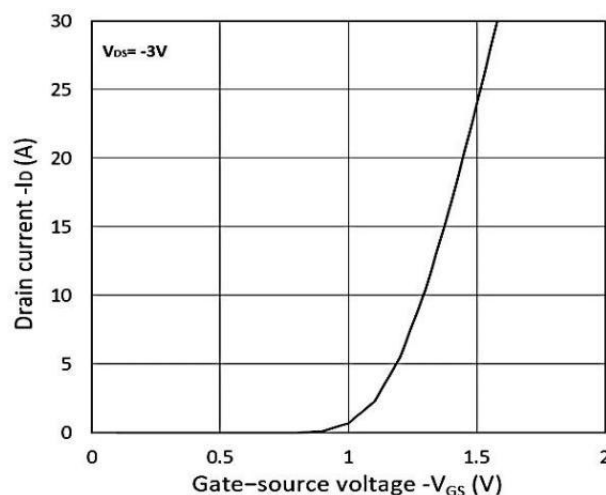


Figure 2. Transfer Characteristics

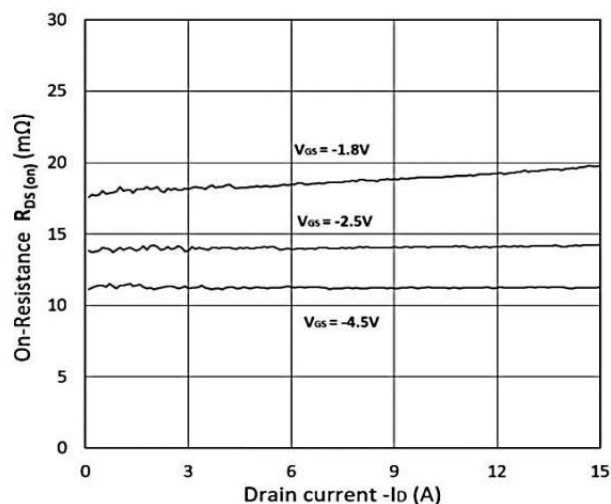


Figure 3. R_DS(ON) vs. I_D

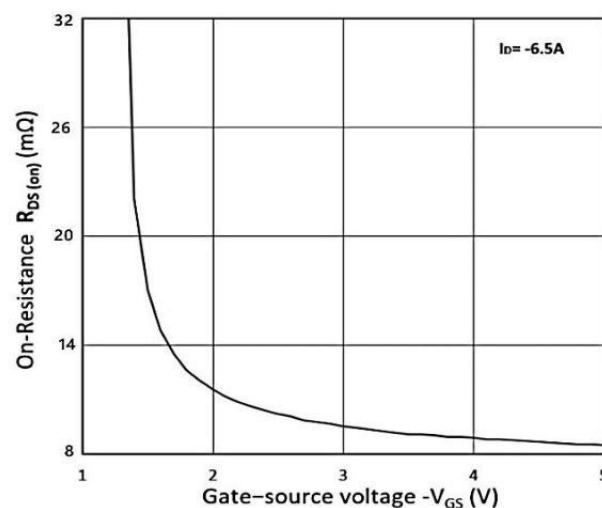


Figure 4. R_DS(ON) vs. V_GS

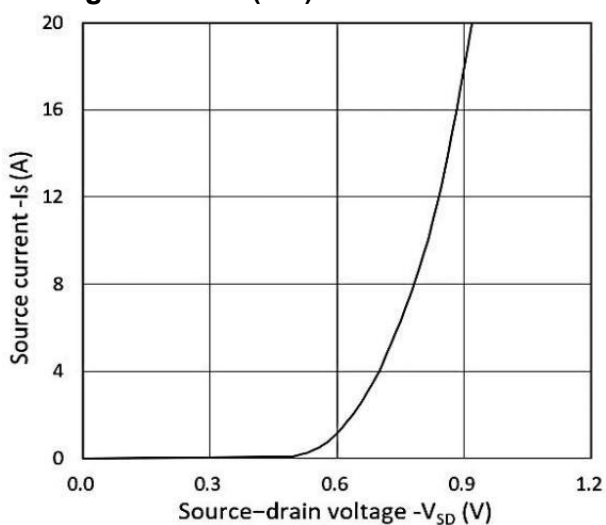


Figure 5. Forward Characteristics of Reverse

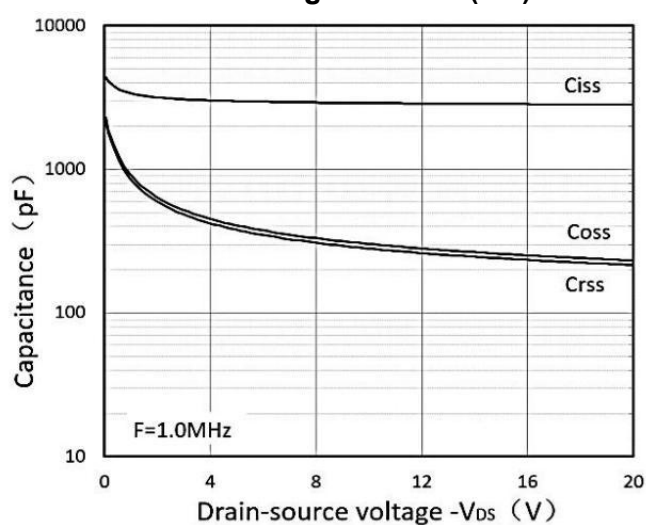


Figure 6. Capacitance Characteristics

Typical Characteristics

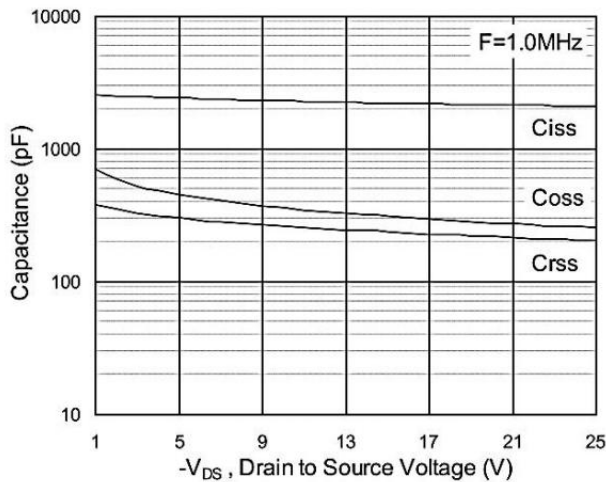


Fig.7 Capacitance

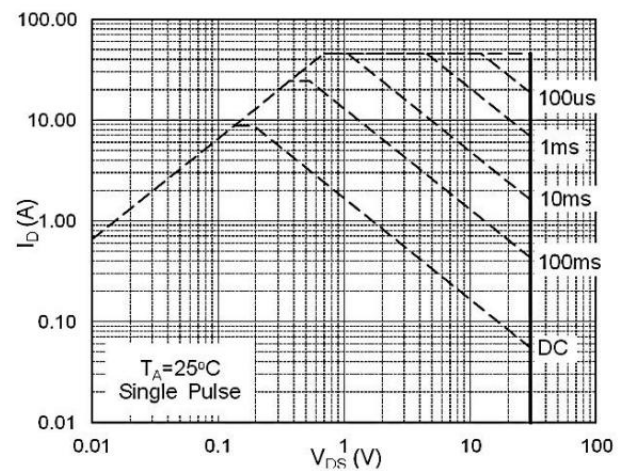


Fig.8 Safe Operating Area

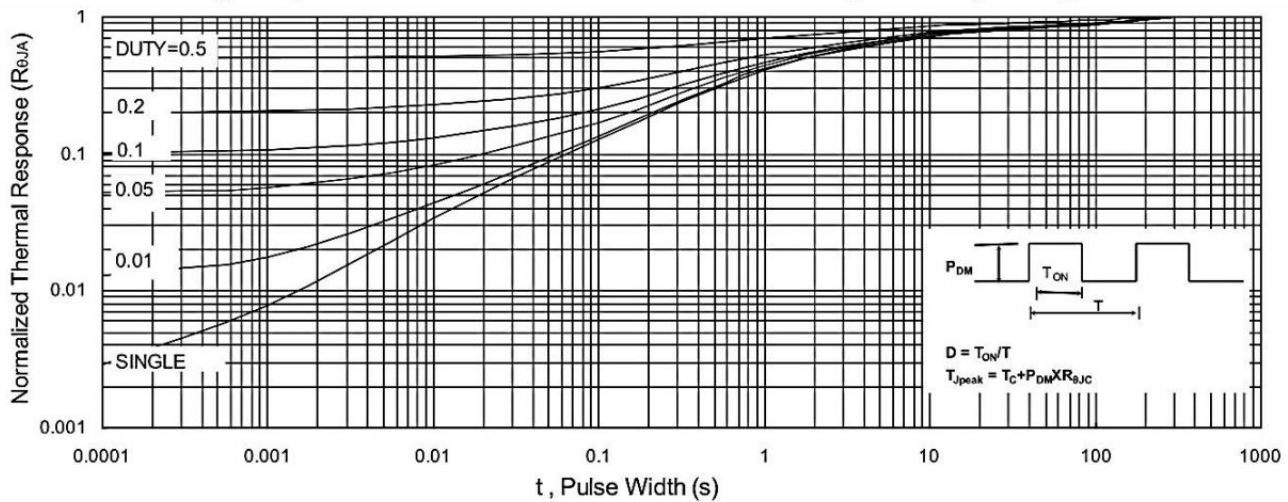


Fig.9 Normalized Maximum Transient Thermal Impedance

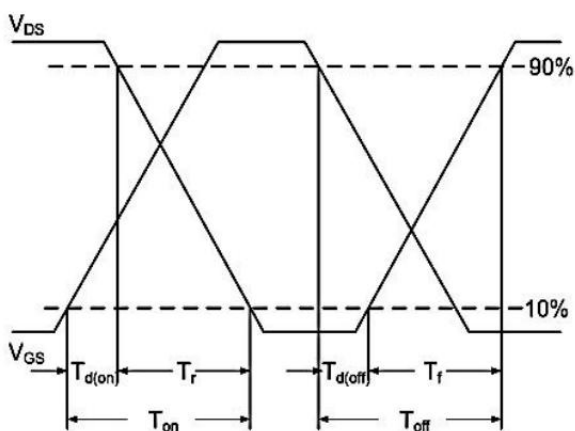


Fig.10 Switching Time Waveform

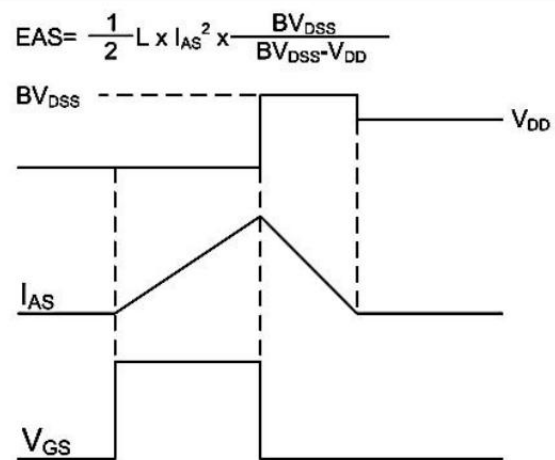
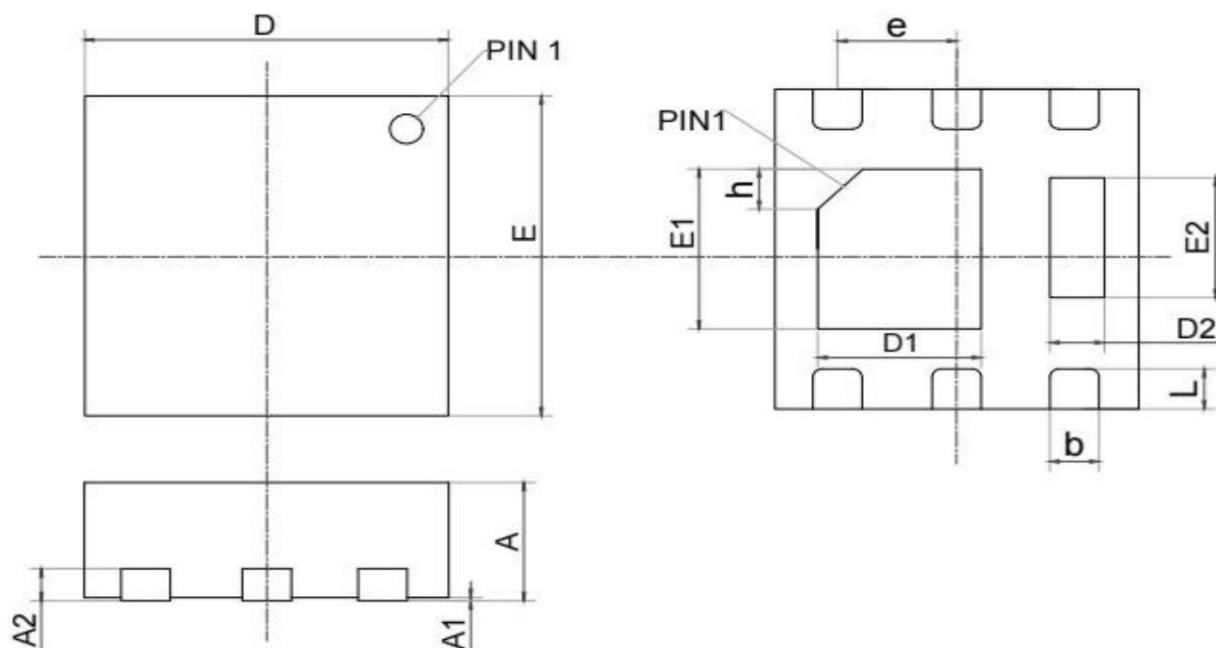


Fig.11 Unclamped Inductive Switching Waveform

Package Mechanical Data: QFN2*2-6L


Symbol			
	Min	Nom	Max
A	0.70	0.75	0.80
A1	--	0.02	0.05
A2	0.18	0.20	0.25
b	0.20	0.27	0.34
D	1.95	2.00	2.05
E	1.95	2.00	2.05
D1	0.80	0.90	1.00
E1	0.90	1.00	1.10
D2	0.20	0.30	0.40
E2	0.65	0.75	0.85
L	0.20	0.25	0.35
h	0.20	0.25	0.30
e	0.65 BSC		

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
TAPING	QFN2*2-6L		3000